



Austin Semiconductor, Inc.

SRAM MT5C1009

128K x 8 SRAM

WITH CHIP & OUTPUT ENABLE

AVAILABLE AS MILITARY SPECIFICATIONS

- SMD 5962-89598
- MIL-STD-883

FEATURES

- Access Times: 15, 20, 25, 35, 45, 55 and 70 ns
- Battery Backup: 2V data retention
- Low power standby
- High-performance, low-power CMOS process
- Single +5V ($\pm 10\%$) Power Supply
- Easy memory expansion with CE\ and OE\ options.
- All inputs and outputs are TTL compatible

OPTIONS

• Timing

15ns access	-15
20ns access	-20
25ns access	-25
35ns access	-35
45ns access	-45
55ns access	-55*
70ns access	-70*

• Package(s)•

Ceramic DIP (400 mil)	C	No. 111
Ceramic DIP (600 mil)	CW	No. 112
Ceramic LCC	EC	No. 207
Ceramic LCC	ECA	No. 208
Ceramic Flatpack	F	No. 303
Ceramic SOJ	DCJ	No. 501
Ceramic SOJ	SOJ	No. 507

- 2V data retention/low power L

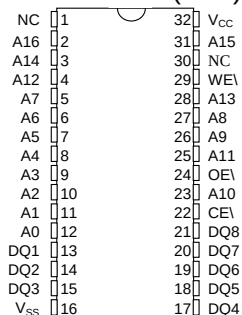
*Electrical characteristics identical to those provided for the 45ns access devices.

**For more products and information
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PIN ASSIGNMENT (Top View)

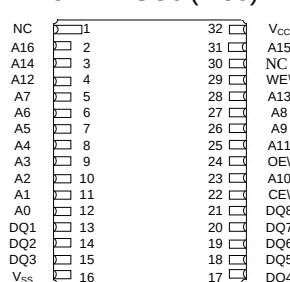
32-Pin DIP (C, CW)

32-Pin SOJ (SOJ)

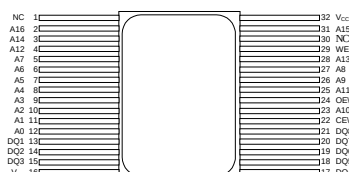


32-Pin LCC (EC)

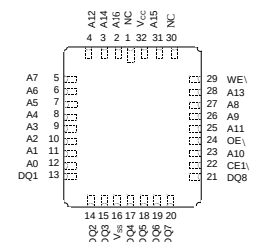
32-Pin SOJ (DCJ)



32-Pin Flat Pack (F)



32-Pin LCC (ECA)



GENERAL DESCRIPTION

The MT5C1009 is a 1,048,576-bit high-speed CMOS static RAM organized as 131,072 words by 8 bits. This device uses 8 common input and output lines and has an output enable pin which operate faster than address access times during READ cycle.

For design flexibility in high-speed memory applications, this device offers chip enable (CE\ and output enable (OE\ features. These enhancements can place the outputs in High-Z for additional flexibility in system design.

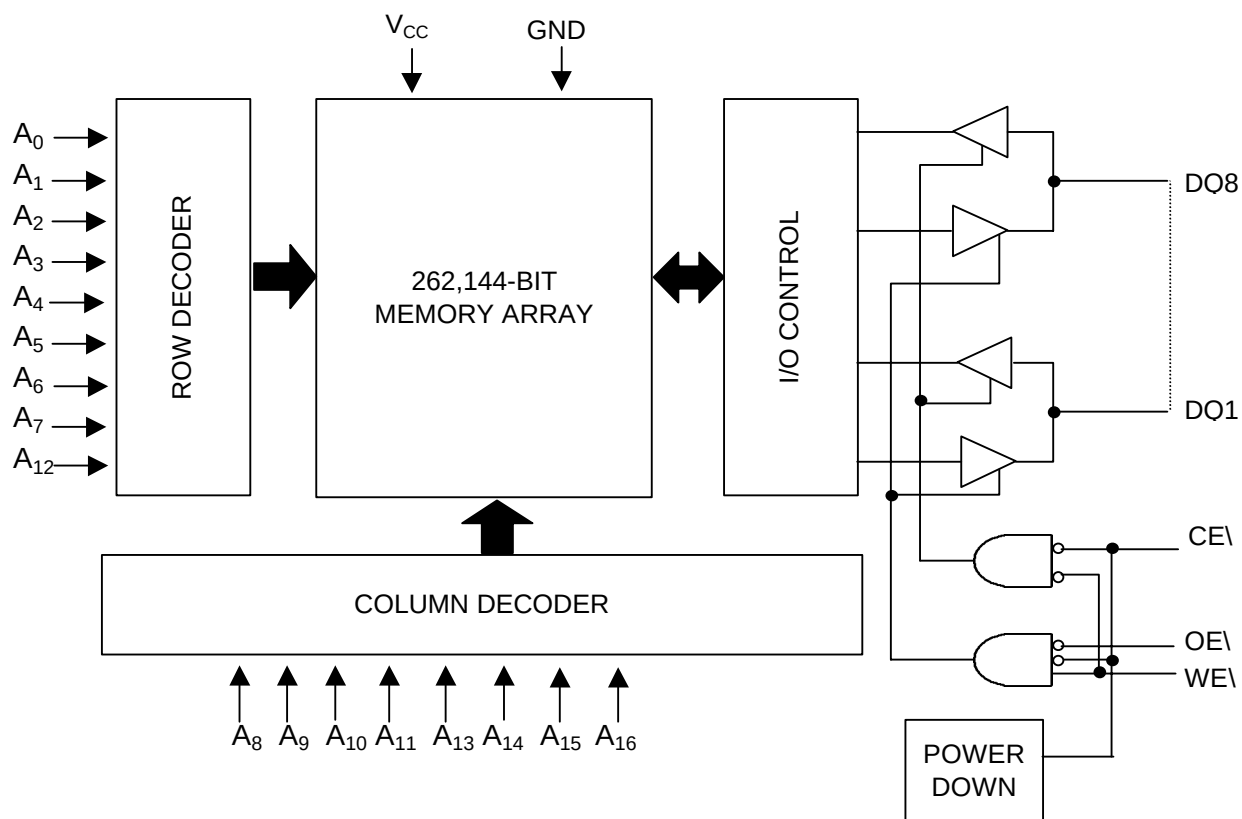
Writing to these devices is accomplished when write enable (WE\ and CE\ inputs are both LOW. Reading is accomplished when WE\ remains HIGH and CE\ and OE\ go LOW. The devices offer a reduced power standby mode when disabled, allowing system designs to achieve low standby power requirements.

The "L" version offers a 2V data retention mode, reducing current consumption to 2mW maximum.

All devices operate from a single +5V power supply and all inputs and outputs are fully TTL compatible. It is particularly well suited for use in high-density, high-speed system applications.



FUNCTIONAL BLOCK DIAGRAM



NOTE: The two least significant row address bits (A8 and A6) are encoded using gray code.

TRUTHTABLE

CE\	WE\	OE\	MODE	I/O PIN	SUPPLY CURRENT
H	X	X	Not Selected	High-Z	I_{SBT2} , I_{SBC2}
X	X	X	Not Selected	High-Z	I_{SBT2} , I_{SBC2}
L	H	H	Output Disable	High-Z	I_{CC}
L	H	L	Read	D_{OUT}	I_{CC}
L	L	X	Write	D_{IN}	I_{CC}



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ABSOLUTE MAXIMUM RATINGS*

Supply Voltage Range (V _{CC}).....	-0.5V to +6.0V
Storage Temperature.....	-65°C to +150°C
Short Circuit Output Current (per I/O).....	20mA
Voltage on any Pin Relative to V _{SS}	-0.5V to +7.0V
Max Junction Temperature**.....	+150°C
Power Dissipation	1 W

*Stresses at or greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods will affect reliability. Refer to page 17 of this datasheet for a technical note on this subject.

** Junction temperature depends upon package type, cycle time, loading, ambient temperature and airflow, and humidity.

ELECTRICAL CHARACTERISTICS AND RECOMMENDED DC OPERATING CONDITIONS

(-55°C ≤ T_J ≤ 125°C & -45°C to +85°C; V_{CC} = 5.0V ±10%)

DESCRIPTION	CONDITIONS	SYM	MIN	MAX	UNITS	NOTES
Input High (Logic 1) Voltage		V _{IH}	2.2	V _{CC} +0.5	V	1
Input Low (Logic 0) Voltage		V _{IL}	-0.5	0.8	V	1, 2
Input Leakage Current	0V ≤ V _{IN} ≤ V _{CC}	I _{LI}	-10	10	μA	
Output Leakage Current	Output(s) disabled 0V ≤ V _{OUT} ≤ V _{CC}	I _{LO}	-10	10	μA	
Output High Voltage	I _{OH} = -4.0mA	V _{OH}	2.4		V	1
Output Low Voltage	I _{OL} = 8.0mA	V _{OL}		0.4	V	1

PARAMETER	CONDITIONS	SYM	MAX					UNITS	NOTES
			-15	-20	-25	-35	-45		
Power Supply Current: Operating	CE\ ≤ V _{IL} ; OE\ = WE\ = V _{IH} , V _{CC} = MAX, f = MAX = 1/t _{RC} (MIN) Output Open	I _{CCSP}	250	140	140	135	125	mA	3
	(1) _L version only	I _{CCLP}	250	140	130	125	115	mA	
Power Supply Current: Standby	CE\ ≥ V _{IH} ; All Other Inputs ≤ V _{IL} or ≥ V _{IH} , V _{CC} = MAX f = 0 Hz	I _{SBT}	25	25	25	25	25	mA	
	CE\ ≥ V _{CC} - 0.2V; V _{CC} = MAX Inputs = V _{IH} or V _{IL} f = 0 Hz	I _{SBCSP}	10	10	10	10	10	mA	
		I _{SBCLP}	10	10	10	10	10	mA	

CAPACITANCE

DESCRIPTION	CONDITIONS	SYM	MAX	UNITS	NOTES
Input Capacitance (A0-A16)	T _A = 25°C, f = 1MHz V _{CC} = 5V	C _I	12	pF	4
Output Capacitance		C _O	20	pF	4
Input Capacitance (CE\, WE\, OE\)		C _I	14	pF	4

**ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS**(Note 5) ($-55^{\circ}\text{C} \leq T_c \leq 125^{\circ}\text{C}$ & -40°C to $+85^{\circ}\text{C}$; $V_{cc} = 5.0\text{V} \pm 10\%$)

DESCRIPTION	SYMBOL	-15		-20		-25		-35		-45		UNITS	NOTES
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
READ CYCLE													
READ cycle time	t _{RC}	15		20		25		35		45		ns	
Address access time	t _{AA}		15		20		25		35		45	ns	
Chip Enable access time	t _{ACE}		15		20		25		35		45	ns	
Output hold from address change	t _{OH}	3		3		3		3		3		ns	
Chip Enable to output in Low-Z	t _{LZCE}	3		3		3		3		3		ns	4, 6, 7
Chip disable to output in High-Z	t _{HZCE}		7		8		10		15		20	ns	4, 6, 7
Output Enable access time	t _{AOE}		7		6		10		15		20	ns	
Output Enable to output in Low-Z	t _{LZOE}	0		0		0		0		0		ns	4, 6, 7
Output disable to output in High-Z	t _{HZOE}		7		6		10		15		20	ns	4, 6, 7
WRITE CYCLE													
WRITE cycle time	t _{WC}	15		20		25		35		45		ns	
Chip Enable to end of write	t _{CW}	12		12		20		25		35		ns	
Address valid to end of write	t _{AW}	12		12		20		25		35		ns	
Address setup time	t _{AS}	0		0		0		0		0		ns	
Address hold from end of write	t _{AH}	0		0		0		0		0		ns	
WRITE pulse width (OE High)	t _{WP}	12		12		20		25		35		ns	
Data setup time	t _{DS}	8		10		15		20		20		ns	
Data hold time	t _{DH}	0		0		0		0		0		ns	
Write disable to output in Low-Z	t _{LZWE}	5		5		5		5		5		ns	4, 6, 7
Write Enable to output in High-Z	t _{HZWE}		7		9		10		15		20	ns	4, 6, 7



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ACTEST CONDITIONS

Input pulse levels	V _{SS} to 3.0V
Input rise and fall times	5ns
Input timing reference levels	1.5V
Output reference levels	1.5V
Output load	See Figures 1 and 2

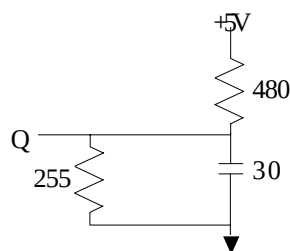


Fig. 1 Output Load Equivalent

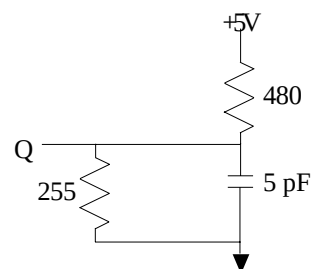


Fig. 2 Output Load Equivalent

NOTES

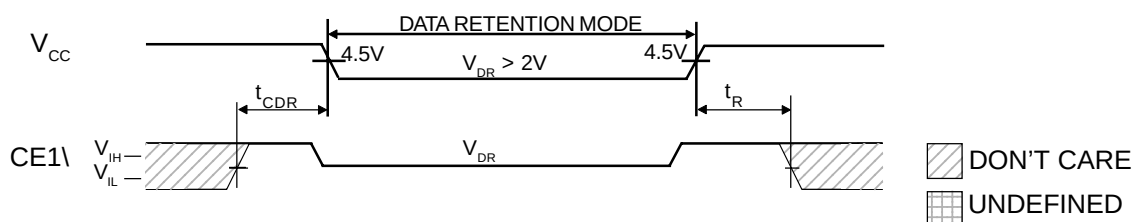
- All voltages referenced to V_{SS} (GND).
- 2V for pulse width < 20ns
- I_{CC} is dependent on output loading and cycle rates. The specified value applies with the outputs unloaded, and f = $\frac{1}{RC (MIN)}$ Hz.
- This parameter is guaranteed but not tested.
- Test conditions as specified with the output loading as shown in Fig. 1 unless otherwise noted.
- 'LZCE, 'LZWE, 'LZOE, 'HZCE, 'HZOE and 'HZWE are specified with CL = 5pF as in Fig. 2. Transition is measured $\pm 200mV$ typical from steady state voltage, allowing for actual tester RC time constant.
- At any given temperature and voltage condition, 'HZCE is less than 'LZCE, and 'HZWE is less than 'LZWE and 'HZOE is less than 'LZOE.
- WE\ is HIGH for READ cycle.
- Device is continuously selected. Chip enables and output enables are held in their active state.
- Address valid prior to, or coincident with, latest occurring chip enable.
- 'RC = Read Cycle Time.

DATA RETENTION ELECTRICAL CHARACTERISTICS (L Version Only)

DESCRIPTION	CONDITIONS		SYMBOL	MIN	MAX	UNITS	NOTES
V _{CC} for Retention Data	$CE \geq (V_{CC} - 0.2V)$ $V_{IN} \geq (V_{CC} - 0.2V)$ or $\leq 0.2V$ $V_{CC} = 2V$		V _{DR}	2	---	V	
Data Retention Current			I _{CCDR1} *		0.75	mA	
			I _{CCDR2}		1.0	mA	
Chip Deselect to Data Retention Time			t _{CDR}	0	---	ns	4
Operation Recovery Time			t _R	t _{RC}		ns	4, 11

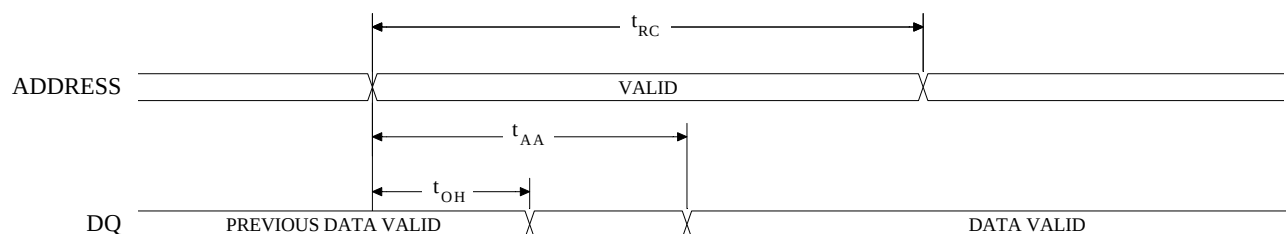
* Low Power, -20 device only

LOW V_{CC} DATA RETENTION WAVEFORM

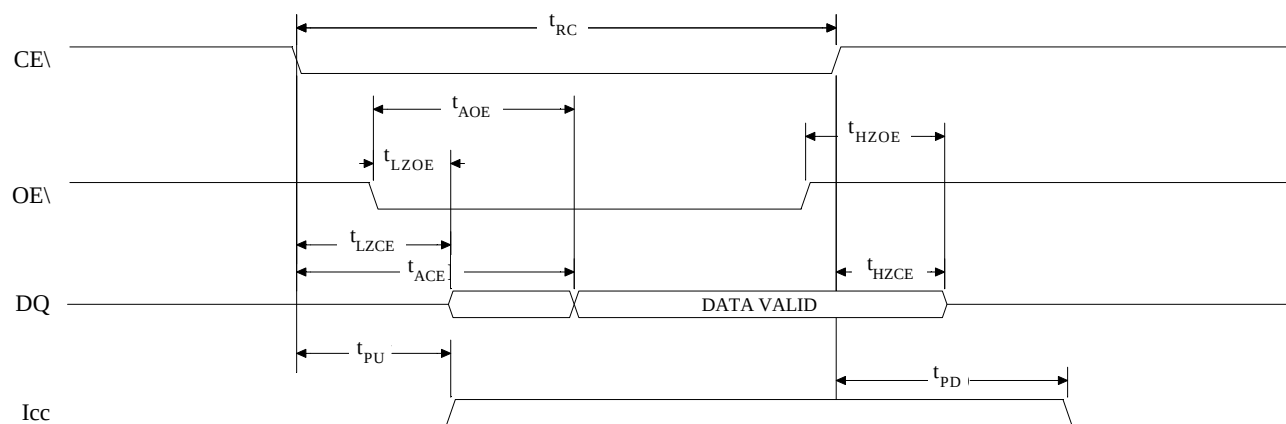




READ CYCLE NO. 1 ^{8,9}

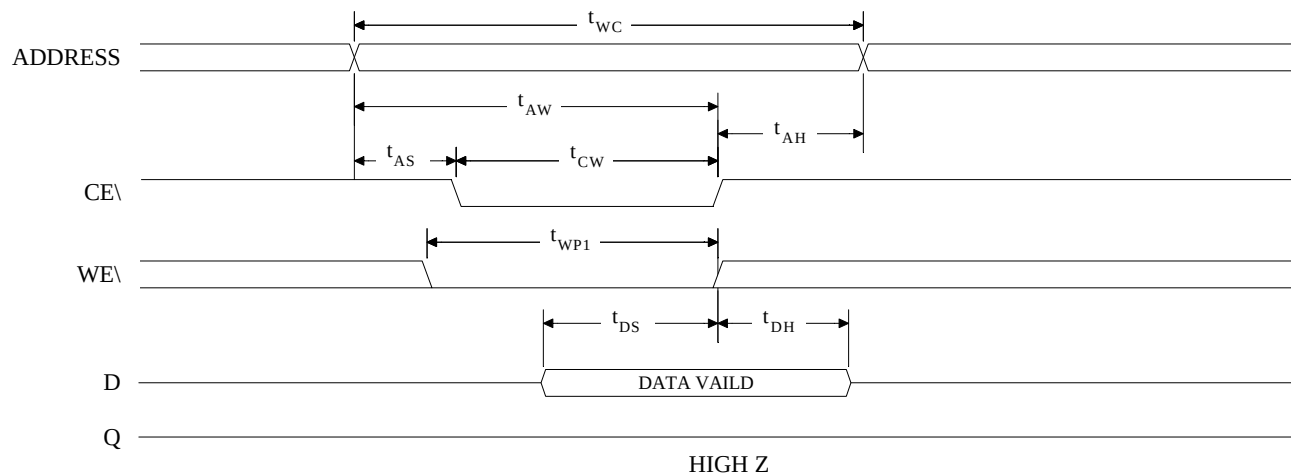


READ CYCLE NO. 2 ^{7, 8, 10, 12}

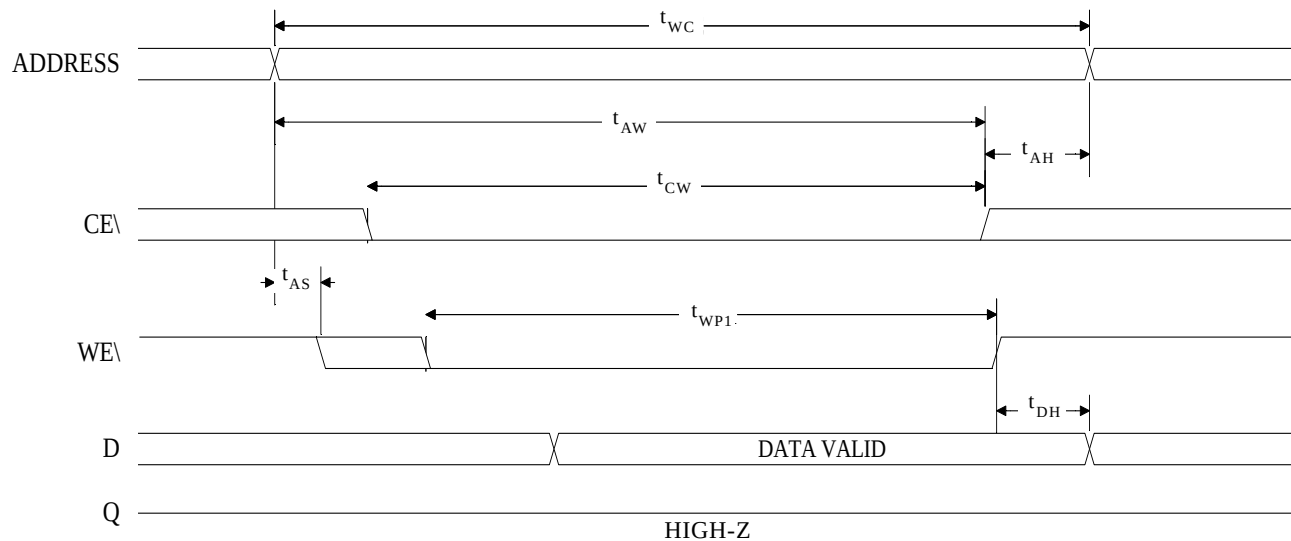




WRITE CYCLE NO. 1 ^{12, 13}
(Chip Enabled Controlled)



WRITE CYCLE NO. 2 ^{7, 12, 13}
(Write Enabled Controlled)



NOTE: Output enable (OE\) is inactive (HIGH).

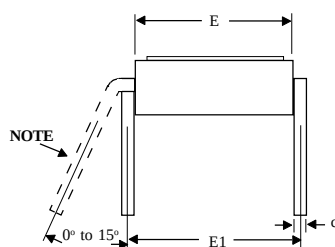
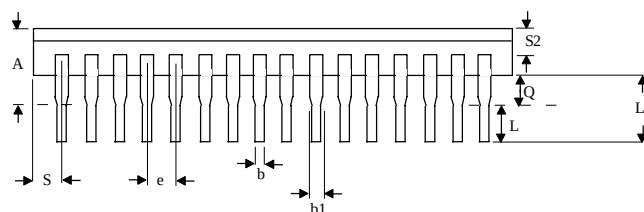
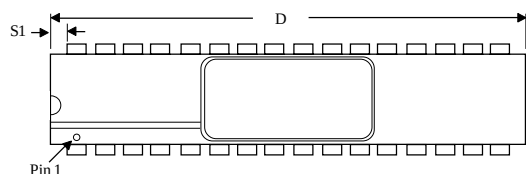


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MECHANICAL DEFINITIONS*

ASI Case #111 (Package Designator C)
SMD 5962-89598, Case Outline Z



SYMBOL	SMD SPECIFICATIONS	
	MIN	MAX
A	---	0.232
b	0.014	0.023
b1	0.038	0.065
c	0.008	0.015
D	---	1.700
E	0.350	0.405
E1	0.390	0.420
e	0.100 BSC	
L	0.125	0.200
L1	0.150	---
Q	0.015	0.060
S	---	0.100
S1	0.005	---
S2	0.005	---
NOTE:	Either configuration in detail A is allowed on SMD.	

*All measurements are in inches.

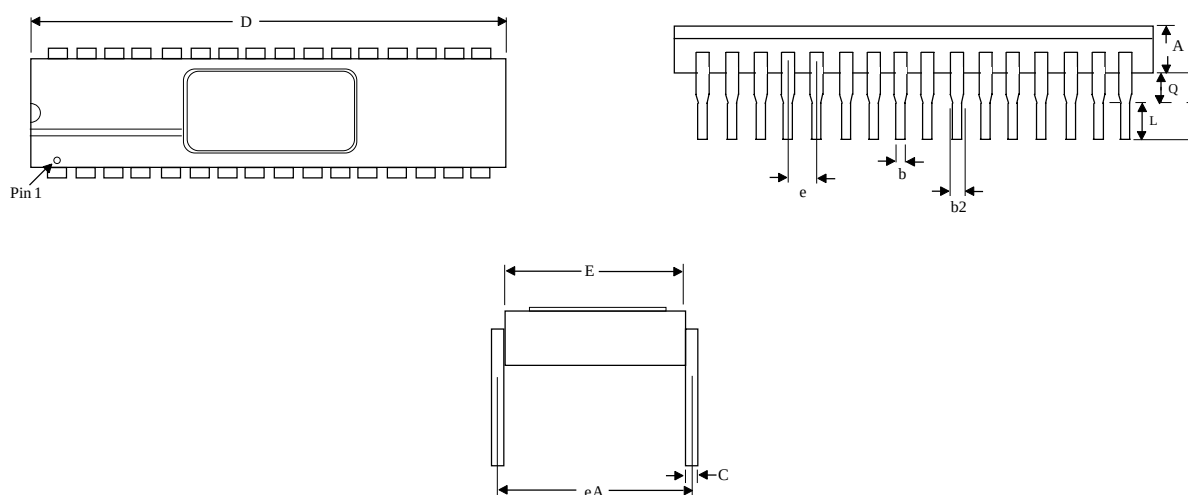


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MECHANICAL DEFINITIONS*

ASI Case #112 (Package Designator CW)
SMD 5962-89598, Case Outline X



SYMBOL	SMD Specifications	
	MIN	MAX
A	0.089	0.111
b	0.016	0.020
b2	0.045	0.050
C	0.009	0.011
D	1.585	1.615
E	0.585	0.605
eA	0.600 BSC	
e	0.100 BSC	
Q	0.040	0.060
L	0.125	0.175

*All measurements are in inches.

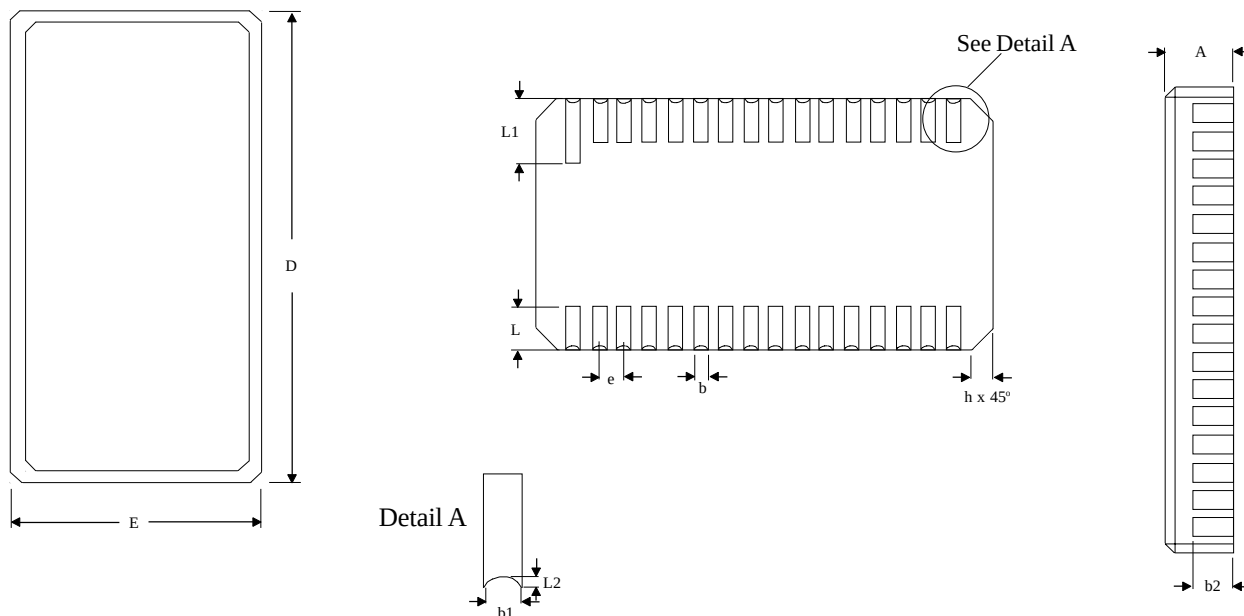


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MECHANICAL DEFINITIONS*

ASI Case #207 (Package Designator EC)
SMD 5962-89598, Case Outline U



SYMBOL	SMD SPECIFICATIONS	
	MIN	MAX
A	0.080	0.100
b	0.022	0.028
b1	0.006	0.022
b2	0.040	---
D	0.800	0.840
E	0.392	0.408
e	0.050 BSC	
h	0.012 REF	
L	0.070	0.080
L1	0.090	0.110
L2	0.003	0.015

*All measurements are in inches.

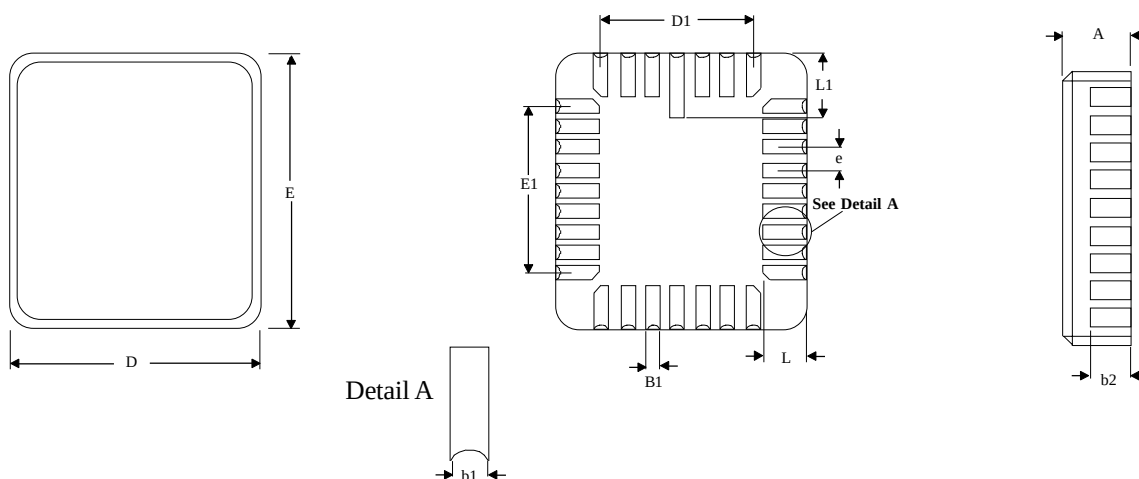


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MECHANICAL DEFINITIONS*

ASI Case #208 (Package Designator ECA)
SMD 5962-89598, Case Outline M



SYMBOL	SMD SPECIFICATIONS	
	MIN	MAX
A	0.060	0.080
B1	0.022	0.028
b1	0.004	0.014
b2	0.040	0.050
D	0.442	0.458
D1	0.300 BSC	
E	0.540	0.560
E1	0.400 BSC	
e	0.050 BSC	
L	0.045	0.055
L1	0.075	0.095

*All measurements are in inches.

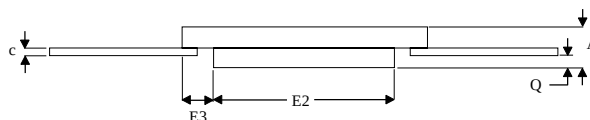
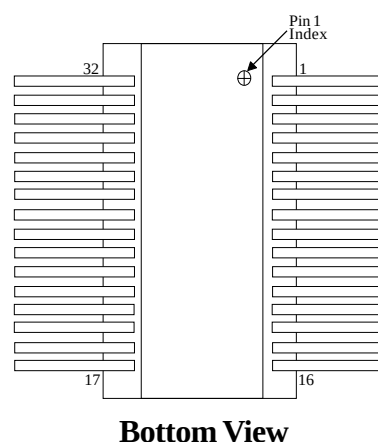
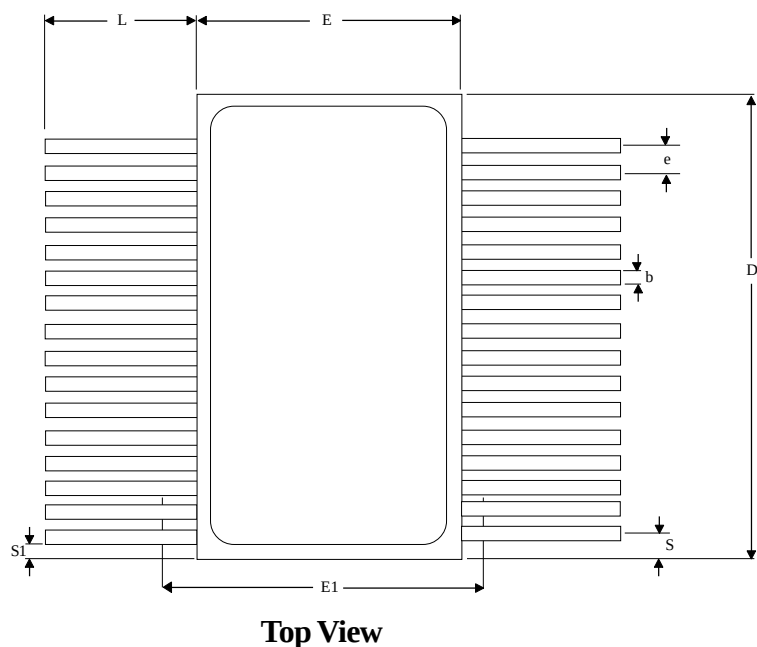


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MECHANICAL DEFINITIONS*

ASI Case #303 (Package Designator F)
SMD 5962-89598, Case Outline T



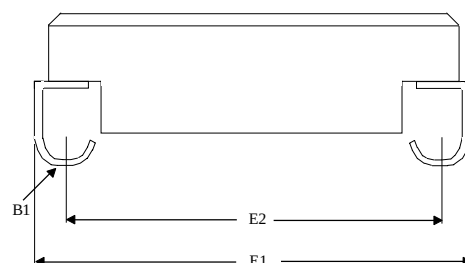
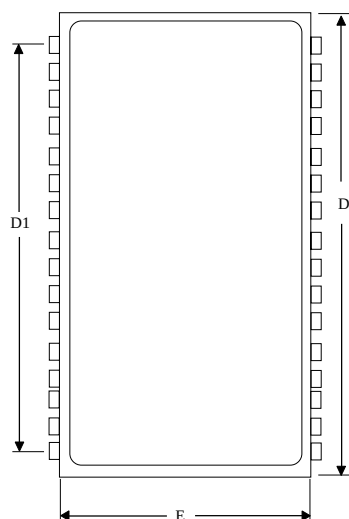
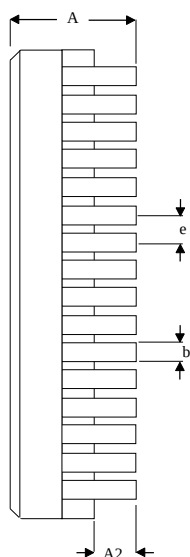
SYMBOL	SMD SPECIFICATIONS	
	MIN	MAX
A	0.097	0.125
b	0.015	0.019
c	0.003	0.009
D	---	0.830
E	0.400	0.420
E1	---	0.450
E2	0.180	---
E3	0.030	---
e	0.050 BSC	
L	0.250	0.370
Q	0.026	0.045
S	---	0.045
S1	0.000	---

*All measurements are in inches.



MECHANICAL DEFINITIONS*

ASI Case #501 (Package Designator DCJ)
SMD 5962-89598, Case Outline 7



SYMBOL	SMD SPECIFICATIONS	
	MIN	MAX
A	0.135	0.144
A2	0.026	0.036
B1	0.030	0.040
b	0.015	0.019
D	0.812	0.828
D1	0.740	0.755
E	0.405	0.415
E1	0.435	0.445
E2	0.360	0.380
e	0.050 BSC	

*All measurements are in inches.

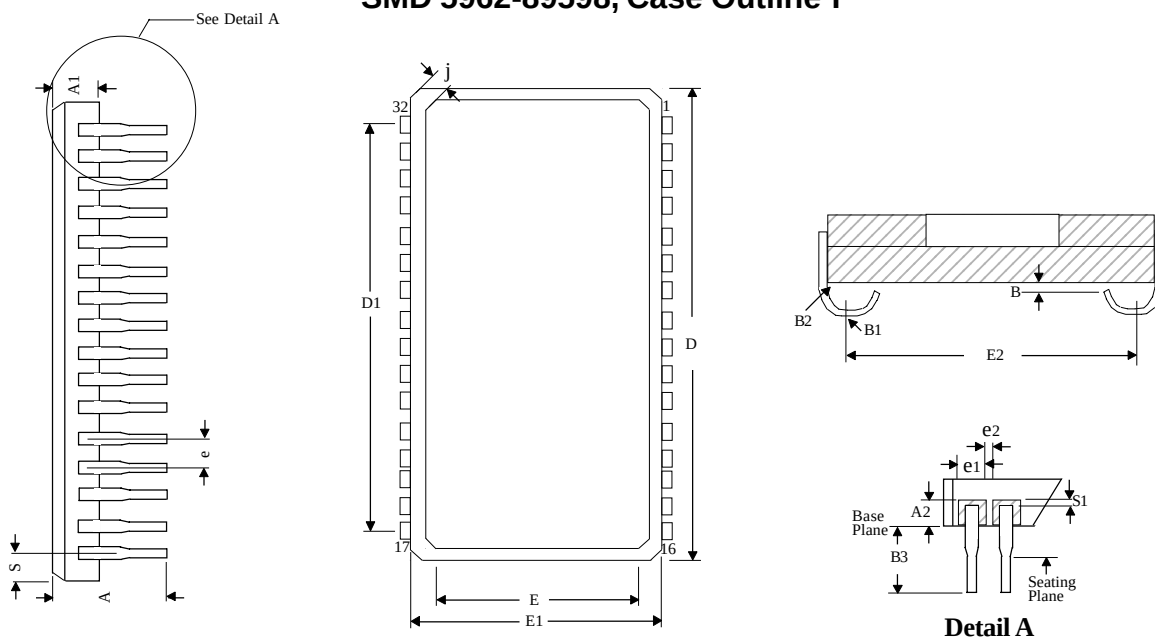


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MECHANICAL DEFINITIONS*

ASI Case #507 (Package Designator SOJ)
SMD 5962-89598, Case Outline Y



SYMBOL	SMD SPECIFICATIONS	
	MIN	MAX
A	0.120	0.165
A1	0.088	0.120
A2	0.070 REF	
B	0.010 REF	
B1	.030R TYP	
B2	0.020 REF	
B3	0.025	0.045
D	0.816	0.838
D1	0.75 REF	
E	0.419	0.431
E1	0.430	0.445
E2	0.360	0.380
e	0.050 BSC	
e1	0.038 TYP	
e2	0.005	
j	0.005 TYP	
S	0.030	0.040
S1	0.020 TYP	

*All measurements are in inches.



Austin Semiconductor, Inc.

SRAM MT5C1009

ORDERING INFORMATION

EXAMPLE: MT5C1009C-25/XT

Device Number	Package Type	Speed ns	Options**	Process
MT5C1009	C	-15	L	/*
MT5C1009	CW	-15	L	/*
MT5C1009	C	-20	L	/*
MT5C1009	CW	-20	L	/*
MT5C1009	C	-25	L	/*
MT5C1009	CW	-25	L	/*
MT5C1009	C	-35	L	/*
MT5C1009	CW	-35	L	/*
MT5C1009	C	-45	L	/*
MT5C1009	CW	-45	L	/*
MT5C1009	C	-55	L	/*
MT5C1009	CW	-55	L	/*
MT5C1009	C	-70	L	/*
MT5C1009	CW	-70	L	/*

EXAMPLE: MT5C1009EC-45L/IT

Device Number	Package Type	Speed ns	Options**	Process
MT5C1009	EC	-15	L	/*
MT5C1009	ECA	-15	L	/*
MT5C1009	EC	-20	L	/*
MT5C1009	ECA	-20	L	/*
MT5C1009	EC	-25	L	/*
MT5C1009	ECA	-25	L	/*
MT5C1009	EC	-35	L	/*
MT5C1009	ECA	-35	L	/*
MT5C1009	EC	-45	L	/*
MT5C1009	ECA	-45	L	/*
MT5C1009	EC	-55	L	/*
MT5C1009	ECA	-55	L	/*
MT5C1009	EC	-70	L	/*
MT5C1009	ECA	-70	L	/*

EXAMPLE: MT5C1009F-70L/883C

Device Number	Package Type	Speed ns	Options**	Process
MT5C1009	F	-15	L	/*
MT5C1009	F	-20	L	/*
MT5C1009	F	-25	L	/*
MT5C1009	F	-35	L	/*
MT5C1009	F	-45	L	/*
MT5C1009	F	-55	L	/*
MT5C1009	F	-70	L	/*

EXAMPLE: MT5C1009DCJ-35/883C

Device Number	Package Type	Speed ns	Options**	Process
MT5C1009	DCJ	-15	L	/*
MT5C1009	SOJ	-15	L	/*
MT5C1009	DCJ	-20	L	/*
MT5C1009	SOJ	-20	L	/*
MT5C1009	DCJ	-25	L	/*
MT5C1009	SOJ	-25	L	/*
MT5C1009	DCJ	-35	L	/*
MT5C1009	SOJ	-35	L	/*
MT5C1009	DCJ	-45	L	/*
MT5C1009	SOJ	-45	L	/*
MT5C1009	DCJ	-55	L	/*
MT5C1009	SOJ	-55	L	/*
MT5C1009	DCJ	-70	L	/*
MT5C1009	SOJ	-70	L	/*

*AVAILABLE PROCESSES

IT = Industrial Temperature Range

XT = Extended Temperature Range

883C = Full Military Processing

-40°C to +85°C

-55°C to +125°C

-55°C to +125°C

** OPTIONS

L = 2V data retention, low power standby



Austin Semiconductor, Inc.

SRAM MT5C1009

ASI TO DSCC PART NUMBER CROSS REFERENCE

ASI Package Designator C & CW

ASI Part #	SMD Part #
MT5C1009C-20/883C	5962-8959839MZA
MT5C1009C-20L/883C	5962-8959840MZA
MT5C1009C-25L/883C	5962-8959812MZA
MT5C1009C-25/883C	5962-8959829MZA
MT5C1009C-35L/883C	5962-8959811MZA
MT5C1009C-35/883C	5962-8959828MZA
MT5C1009C-45L/883C	5962-8959810MZA
MT5C1009C-45/883C	5962-8959827MZA
MT5C1009C-55L/883C	5962-8959809MZA
MT5C1009C-55/883C	5962-8959826MZA
MT5C1009C-70L/883C	5962-8959808MZA
MT5C1009C-70/883C	5962-8959825MZA
MT5C1009CW-20/883C	5962-8959839MXA
MT5C1009CW-20L/883C	5962-8959840MXA
MT5C1009CW-25L/883C	5962-8959812MXA
MT5C1009CW-25/883C	5962-8959829MXA
MT5C1009CW-35L/883C	5962-8959811MXA
MT5C1009CW-35/883C	5962-8959828MXA
MT5C1009CW-45L/883C	5962-8959810MXA
MT5C1009CW-45/883C	5962-8959827MXA
MT5C1009CW-55L/883C	5962-8959809MXA
MT5C1009CW-55/883C	5962-8959826MXA
MT5C1009CW-70L/883C	5962-8959808MXA
MT5C1009CW-70/883C	5962-8959825MXA

ASI Package Designator EC & ECA

ASI Part #	SMD Part #
MT5C1009EC-20/883C	5962-8959839MUA
MT5C1009EC-20L/883C	5962-8959840MUA
MT5C1009EC-25L/883C	5962-8959812MUA
MT5C1009EC-25/883C	5962-8959829MUA
MT5C1009EC-35L/883C	5962-8959811MUA
MT5C1009EC-35/883C	5962-8959828MUA
MT5C1009EC-45L/883C	5962-8959810MUA
MT5C1009EC-45/883C	5962-8959827MUA
MT5C1009EC-55L/883C	5962-8959809MUA
MT5C1009EC-55/883C	5962-8959826MUA
MT5C1009EC-70L/883C	5962-8959808MUA
MT5C1009EC-70/883C	5962-8959825MUA
MT5C1009ECA-20/883C	5962-8959839MMA
MT5C1009ECA-20L/883C	5962-8959840MMA
MT5C1009ECA-25L/883C	5962-8959812MMA
MT5C1009ECA-25/883C	5962-8959829MMA
MT5C1009ECA-35L/883C	5962-8959811MMA
MT5C1009ECA-35/883C	5962-8959828MMA
MT5C1009ECA-45L/883C	5962-8959810MMA
MT5C1009ECA-45/883C	5962-8959827MMA
MT5C1009ECA-55L/883C	5962-8959809MMA
MT5C1009ECA-55/883C	5962-8959826MMA
MT5C1009ECA-70L/883C	5962-8959808MMA
MT5C1009ECA-70/883C	5962-8959825MMA

ASI Package Designator F

ASI Part #	SMD Part #
MT5C1009F-20/883C	5962-8959839MTA
MT5C1009F-20L/883C	5962-8959840MTA
MT5C1009F-25L/883C	5962-8959812MTA
MT5C1009F-25/883C	5962-8959829MTA
MT5C1009F-35L/883C	5962-8959811MTA
MT5C1009F-35/883C	5962-8959828MTA
MT5C1009F-45L/883C	5962-8959810MTA
MT5C1009F-45/883C	5962-8959827MTA
MT5C1009F-55L/883C	5962-8959809MTA
MT5C1009F-55/883C	5962-8959826MTA
MT5C1009F-70L/883C	5962-8959808MTA
MT5C1009F-70/883C	5962-8959825MTA

ASI Package Designator DCJ

ASI Part #	SMD Part #
MT5C1009DCJ-20/883C	5962-8959839M7A
MT5C1009DCJ-20L/883C	5962-8959840M7A
MT5C1009DCJ-25L/883C	5962-8959812M7A
MT5C1009DCJ-25/883C	5962-8959829M7A
MT5C1009DCJ-35L/883C	5962-8959811M7A
MT5C1009DCJ-35/883C	5962-8959828M7A
MT5C1009DCJ-45L/883C	5962-8959810M7A
MT5C1009DCJ-45/883C	5962-8959827M7A
MT5C1009DCJ-55L/883C	5962-8959809M7A
MT5C1009DCJ-55/883C	5962-8959826M7A
MT5C1009DCJ-70L/883C	5962-8959808M7A
MT5C1009DCJ-70/883C	5962-8959825M7A

ASI Package Designator SOJ

ASI Part #	SMD Part #
MT5C1009SOJ-20/883C	5962-8959839M7A
MT5C1009SOJ-20L/883C	5962-8959840M7A
MT5C1009SOJ-25L/883C	5962-8959812M7A
MT5C1009SOJ-25/883C	5962-8959829M7A
MT5C1009SOJ-35L/883C	5962-8959811M7A
MT5C1009SOJ-35/883C	5962-8959828M7A
MT5C1009SOJ-45L/883C	5962-8959810M7A
MT5C1009SOJ-45/883C	5962-8959827M7A
MT5C1009SOJ-55L/883C	5962-8959809M7A
MT5C1009SOJ-55/883C	5962-8959826M7A
MT5C1009SOJ-70L/883C	5962-8959808M7A
MT5C1009SOJ-70/883C	5962-8959825M7A

* ASI part number is for reference only. Orders received referencing the SMD part number will be processed per the SMD.



DATE: 2/6/01

Technical Note:

128Kx8 SRAM – Maximum Recommended Supply Voltage and Ambient Temperature

Compliance:

This product fully meets and is tested in compliance with SMD# 5962-89598 and tested in accordance with JESD78.

Specific Product Affected:

Die Manufacturer: Alliance Semiconductor Corporation

Die Name: AS2008SA

Device Types: MT5C1008 , MT5C1009

Speed Grades: All

Package Designators: All

Identifying Date Code Marking: Change implemented on product starting with date code 0100.

Characteristic Identified:

Austin Semiconductor, Inc. has received notification from this die vendor, Alliance Semiconductor Corp., that operation at high Vcc's of 6 volts and beyond may result in a latch-up condition. This can cause permanent damage to the device.

Recommendation:

During use in system applications and during manufacturing processes, including Burn-In and Test, the devices should not be subjected to Vcc Supply Voltages higher than 5.5Volts at 125°C.